

InGaAs PIN Module

Features

Active diameter 2000um

Small dark current

High reliability

Applications

Fiberoptics telecommunication networks

Digital receivers

Optical interconnects

Test and measurement

Datacom

Absolute maximum ratings

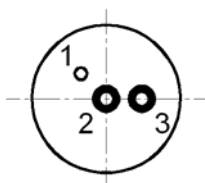
Parameter	Symbol	Value	Unit
Storage temperature	T _{st}	-40~+85	°C
Operating temperature	T _{op}	-40~+85	°C
Reverse voltage	V _R	30	V
Soldering temperature/time	—	260/10	°C/ s

Optical & electrical characteristics(T=25°C)

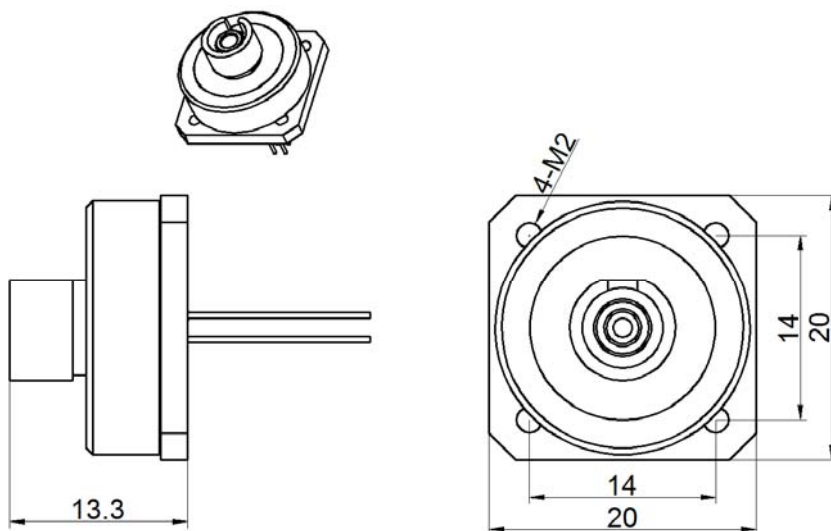
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Detection range	λ	1100	-	1650	nm	-
Dark current	I _d	-	1	5	nA	V _R =5V
Quantum efficiency	R	0.80	0.85	-	A/W	V _R =5V, λ =1310 nm
Capacitance	C _t	-	-	0.75	pF	V _R =5V

Dimensions Diagram

PIN assignment



pin	Function
1(case)	GND
2	N
3	P



This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures



Order information

D	1	20	X	C
			Range 0,-70~+6dBm 1, -60~+10dBm 2, -50~+20dBm	Package D,D